## Marzaini Rashid

List of Publications by Year in descending order

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1040056 996975 23 232 9 15 citations h-index g-index papers 23 23 23 274 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	High-performance multicolor metal-semiconductor-metal Si photodetector enhanced by nanostructured NiO thin film. Journal of Alloys and Compounds, 2019, 798, 300-310.	5.5	45
2	Control of the structural, electrical and optical properties of spin coated NiO films by varying precursor molarity. Thin Solid Films, 2019, 690, 137554.	1.8	24
3	VIS-NIR spectral and particles distribution of Au, Ag, Cu, Al and Ni nanoparticles synthesized in distilled water using laser ablation. Results in Physics, 2019, 14, 102497.	4.1	20
4	ZnO quantum dot based thin films as promising electron transport layer: Influence of surface-to-volume ratio on the photoelectric properties. Ceramics International, 2021, 47, 12397-12409.	4.8	18
5	pn-Junction photodiode based on GaN grown on Si (111) by plasma-assisted molecular beam epitaxy. Materials Science in Semiconductor Processing, 2013, 16, 1859-1864.	4.0	14
6	Surface-state dependent optical properties of OH-, F-, and H-terminated 4H-SiC quantum dots. Physical Chemistry Chemical Physics, 2016, 18, 21676-21685.	2.8	12
7	Optical properties of mesoporous 4H-SiC prepared by anodic electrochemical etching. Journal of Applied Physics, 2016, 120, .	2.5	10
8	Broadband visible emission from photoelectrochemical etched porous silicon quantum dots containing zinc. Materials Chemistry and Physics, 2021, 258, 123935.	4.0	10
9	Eco-friendly ultrafast self-powered p-Si/n-ZnO photodetector enhanced by photovoltaic-pyroelectric coupling effect. Ceramics International, 2022, 48, 16142-16155.	4.8	10
10	Preparation and characteristics study of self-powered and fast response p-NiO/n-Si heterojunction photodetector. Ceramics International, 2022, 48, 20078-20089.	4.8	10
11	Structural, optical and electrical investigation of low-temperature processed zinc oxide quantum dots based thin films using precipitation-spin coating on flexible substrates. Physica B: Condensed Matter, 2022, 635, 413806.	2.7	9
12	White, blue and green emission from Si QDs derived from zinc incorporated porous silicon. Journal of Luminescence, 2021, 232, 117845.	3.1	8
13	Multi – wavelength photodetectors based on porous spin-coated and compact RF-sputtered NiO films grown over Si substrate: Effect of surface morphology. Optik, 2022, 255, 168694.	2.9	8
14	Low power consumption UV sensor based on n-ZnO/p-Si junctions. Journal of Materials Science: Materials in Electronics, 2019, 30, 19639-19646.	2.2	6
15	Silicon quantum dot/black silicon hybrid nanostructure for broadband reflection reduction. Materials Science in Semiconductor Processing, 2020, 115, 105113.	4.0	6
16	Mesoporous TiO2 Implanted ZnO QDs for the Photodegradation of Tetracycline: Material Design, Structural Characterization and Photodegradation Mechanism. Catalysts, 2021, 11, 1205.	3.5	6
17	Concentration dependence of physical properties of low temperature processed ZnO quantum dots thin films on polyethylene terephthalate as potential electron transport material for perovskite solar cell. Ceramics International, 2022, 48, 31559-31569.	4.8	6
18	Photovoltaic Performance of Spherical TiO2 Nanoparticles Derived from Titanium Hydroxide Ti(OH)4: Role of Annealing Varying Temperature. Energies, 2022, 15, 1648.	3.1	4

#	Article	IF	CITATIONS
19	Effect of RF power on structural, morphological and optical properties of NiO thin films. AIP Conference Proceedings, 2019, , .	0.4	2
20	Enhancement of Temperature Fluorescence Brightness of Zn@Si Core-Shell Quantum Dots Produced via a Unified Strategy. Nanomaterials, 2021, 11, 3158.	4.1	2
21	Tuning Optoelectronic Properties of 4H-SiC QDs Using -H, -OH and -F Surface Functionalisation. Materials Science Forum, 0, 821-823, 375-378.	0.3	1
22	Pore Wall Thinning of Mesoporous 4Hâ€SiC by Sacrificial Oxidation. Crystal Research and Technology, 2018, 53, 1800120.	1.3	1
23	Characterization of SiO2/SiC Interface of Phosphorous-Doped MOS Capacitors by Conductance Measurements. International Journal of Recent Technology and Engineering, 2019, 8, 5505-5508.	0.2	O